Sheet 1 of 1

INFORMATION DISCLOSURE CITATION IN AN APPLICATION (Use several sheets if necessary)				Attorney Docket No.: 8022-1094			Application No.:10/529,851 NEW NATIONAL PHASE			
				Applicant: Katsumi SUEMITSU t al.						
				Filing Date: March 31, 2005			Group Art Unit: 2809			
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EXAMINER: /Jami Valentine/				DATE CONSIDERED 01/29/2007						
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if										

^{*} English language abstract provided for the Examiner's convenience